

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Tae-Hee CHOE, et al.

Serial No.

*[Division of Serial No. 09/989,112, filed November 21, 2001]*

Filed: November 17, 2003

For: SOI SUBSTRATE HAVING AN ETCH STOP LAYER, AND FABRICATION METHOD THEREOF,  
SOI INTEGRATED CIRCUIT FABRICATED THEREON, AND METHOD OF FABRICATING  
SOI INTEGRATED CIRCUIT USING THE SAME

**CONFIRMATION**  
**CLAIM FOR CONVENTION PRIORITY**

Commissioner for Patents  
Alexandria, VA 22313-1450

Sir:

The benefit of the filing date of the following prior foreign application filed in the following foreign country is hereby requested, and the right of priority provided in 35 U.S.C. §119 is hereby claimed:

**Application No. 2001-28008 - filed May 22, 2001 - Republic of Korea**

In support of this claim, a certified copy of said original foreign application was filed in parent application Serial No. 09/989,112 on November 21, 2001.

Acknowledgment of applicant's claim for priority and receipt of the certified priority document is solicited.

Respectfully submitted,

Date: November 17, 2003

  
Eugene M. Lee, Reg. No. 32,039

LEE & STERBA, P.C.  
1101 WILSON BOULEVARD, SUITE 2000  
ARLINGTON, VA 22209  
703.525.0978 TEL  
703.525.4265 FAX